



## JCD10SL120A SiC Schottky Diode

Rev.1.3

### DESCRIPTION

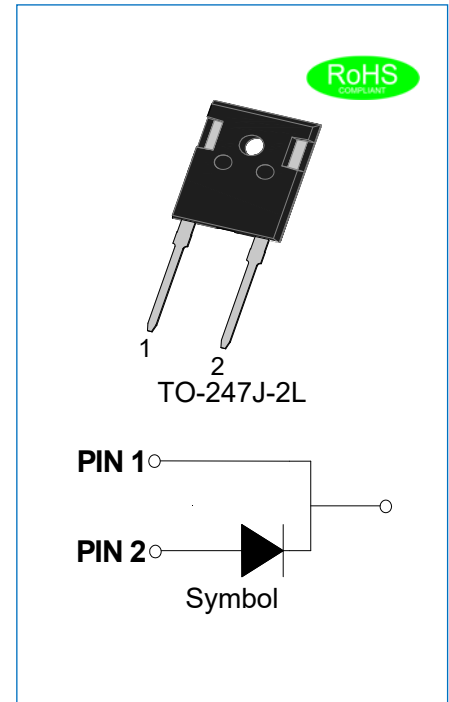
- ✧ 1200V Schottky diode
- ✧ Zero reverse recovery current
- ✧ Zero forward recovery voltage
- ✧ High frequency operation
- ✧ Switching characteristics independent of temperature
- ✧ Fast switch
- ✧ Positive temperature coefficient of forward voltage ( $V_F$ )

### BENEFIT

- ✧ Lower switching loss
- ✧ No thermal runaway in parallel devices
- ✧ Lower heatsink dependent

### APPLICATION

- ✧ Switch mode power supplies(SMPS)
- ✧ Boost diodes in PFC or DC/DC stages
- ✧ Free wheeling diodes in inverter stages
- ✧ AC/DC converters



### ABSOLUTE MAXIMUM RATING (Rating at 25°C junction temperature unless otherwise specified.)

| Parameter                                        |                                                           | Symbol         | Value       | Unit               |
|--------------------------------------------------|-----------------------------------------------------------|----------------|-------------|--------------------|
| Maximum repetitive peak reverse voltage          |                                                           | $V_{RRM}$      | 1200        | V                  |
| Maximum DC blocking voltage                      |                                                           | $V_{DC}$       | 1200        | V                  |
| Average forward current                          | $T_C=150^{\circ}\text{C}$                                 | $I_{F(AV)}$    | 10          | A                  |
| Repetitive peak forward surge current            | $t_P=10\text{ms}, T_C=25^{\circ}\text{C}$                 | $I_{FRM}$      | 50          | A                  |
| Non-repetitive peak forward surge current        | $t_P=10\text{ms}, T_C=25^{\circ}\text{C}$                 | $I_{FSM}$      | 80          | A                  |
| Non-repetitive peak forward surge current        | $T_C=25^{\circ}\text{C}, t_P=10\mu\text{s}, \text{Pulse}$ | $I_{FMax}$     | 600         | A                  |
| Power dissipation                                | $T_C=25^{\circ}\text{C}$                                  | $P_{tot}$      | 205         | W                  |
|                                                  | $T_C=110^{\circ}\text{C}$                                 |                | 90          |                    |
| Operating junction and storage temperature range |                                                           | $T_J, T_{STG}$ | -55 to +175 | $^{\circ}\text{C}$ |

**ELECTRICAL CHARACTERISTICS**(Rating at 25°C junction temperature unless otherwise specified.)

| Parameter                 | Conditions                    | Symbol | Value |      |      | Unit    |
|---------------------------|-------------------------------|--------|-------|------|------|---------|
|                           |                               |        | Min.  | Typ. | Max. |         |
| Forward voltage           | $I_F=10A, T_J=25^{\circ}C$    | $V_F$  | -     | 1.5  | 1.8  | V       |
|                           | $I_F=10A, T_J=175^{\circ}C$   |        | -     | 2.2  | 3.0  |         |
| Reverse current           | $V_R=1200V, T_J=25^{\circ}C$  | $I_R$  | -     | 10   | 50   | $\mu A$ |
|                           | $V_R=1200V, T_J=175^{\circ}C$ |        | -     | 20   | 100  |         |
| Total capacitance         | $V_R=0V, f=1MHz$              | C      | -     | 610  | -    | pF      |
|                           | $V_R=400V, f=1MHz$            |        | -     | 46   | -    |         |
|                           | $V_R=800V, f=1MHz$            |        | -     | 36   | -    |         |
| Total capacitance charge  | $V_R=800V, T_J=25^{\circ}C$   | $Q_C$  | -     | 50   | -    | nC      |
| Capacitance stored energy | $V_R=800V$                    | $E_C$  | -     | 25   | -    | $\mu J$ |

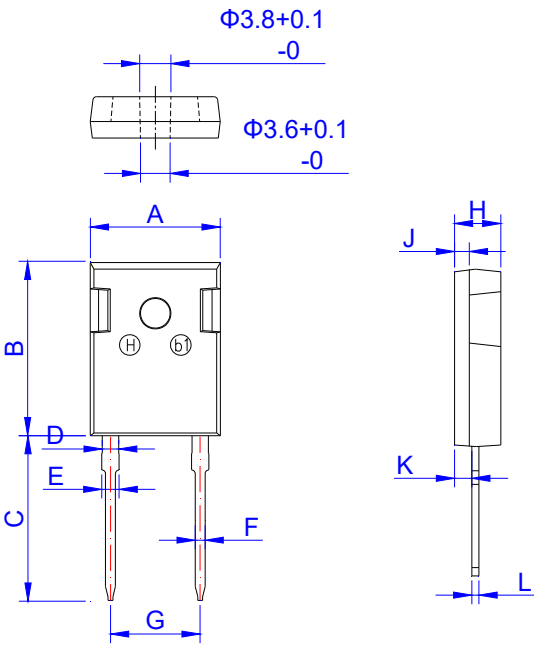
**THERMAL CHARACTERISTICS**

| Symbol        | Parameter        | Value | Unit          |
|---------------|------------------|-------|---------------|
| $R_{th(j-c)}$ | Junction to case | 0.73  | $^{\circ}C/W$ |

**ORDERING INFORMATION**

|                                  |                    |               |                |                 |           |
|----------------------------------|--------------------|---------------|----------------|-----------------|-----------|
| J                                | CD                 | 10            | SL             | 120             | A         |
| JieJie Microelectronics Co., Ltd | SiC Schottky Diode | $I_F(AV)=10A$ | SL: TO-247J-2L | $V_{RRM}:1200V$ | Version A |

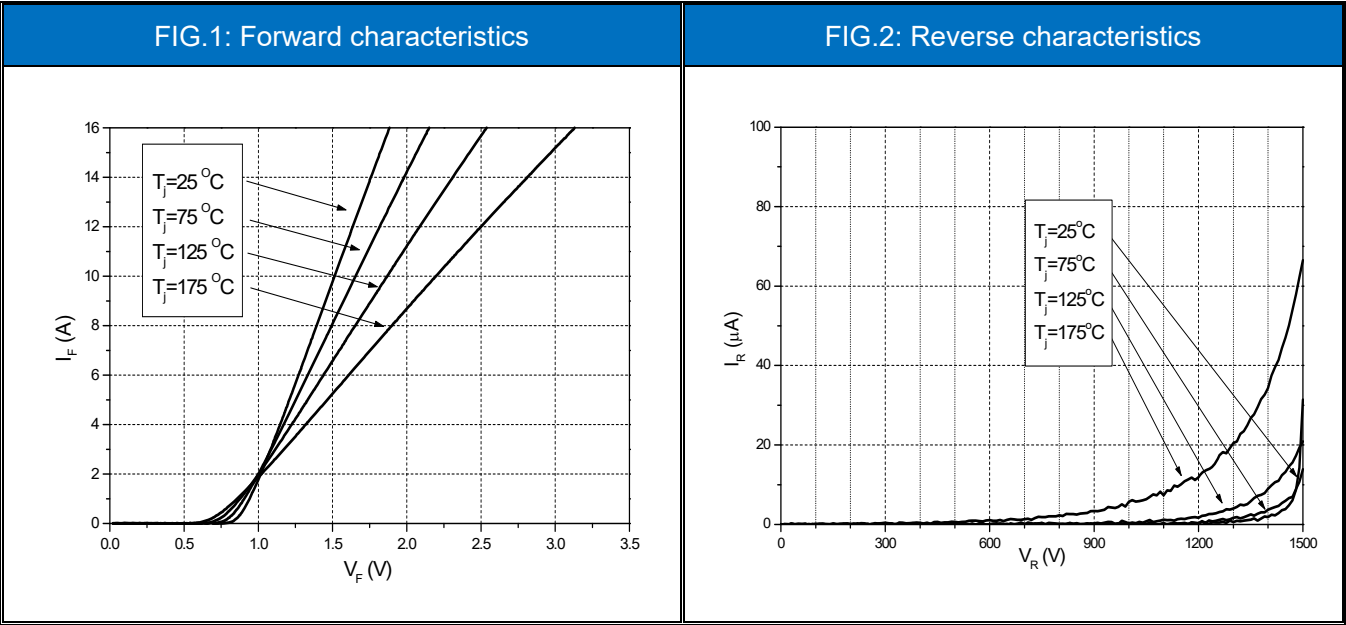
PACKAGE MECHANICAL DATA



TO-247J-2L

| Ref. | Dimensions  |       |       |        |       |       |
|------|-------------|-------|-------|--------|-------|-------|
|      | Millimeters |       |       | Inches |       |       |
|      | Min.        | Typ.  | Max.  | Min.   | Typ.  | Max.  |
| A    | 15.50       | 15.80 | 16.10 | 0.610  | 0.622 | 0.634 |
| B    | 20.80       | 21.00 | 21.20 | 0.819  | 0.827 | 0.835 |
| C    | 19.70       | 20.00 | 20.30 | 0.776  | 0.787 | 0.799 |
| D    | 1.80        | 2.00  | 2.20  | 0.071  | 0.079 | 0.087 |
| E    | 1.90        | 2.10  | 2.30  | 0.075  | 0.083 | 0.091 |
| F    | 1.00        | 1.20  | 1.40  | 0.039  | 0.047 | 0.055 |
| G    | 10.50       |       | 11.30 | 0.413  |       | 0.445 |
| H    | 4.80        | 5.00  | 5.20  | 0.189  | 0.197 | 0.205 |
| J    | 1.90        | 2.00  | 2.10  | 0.075  | 0.079 | 0.083 |
| K    | 2.20        | 2.35  | 2.50  | 0.087  | 0.093 | 0.098 |
| L    | 0.41        | 0.60  | 0.79  | 0.016  | 0.024 | 0.031 |

CHARACTERISTICS CURVE



## CHARACTERISTICS CURVE

FIG.3: Capacitance vs. reverse voltage

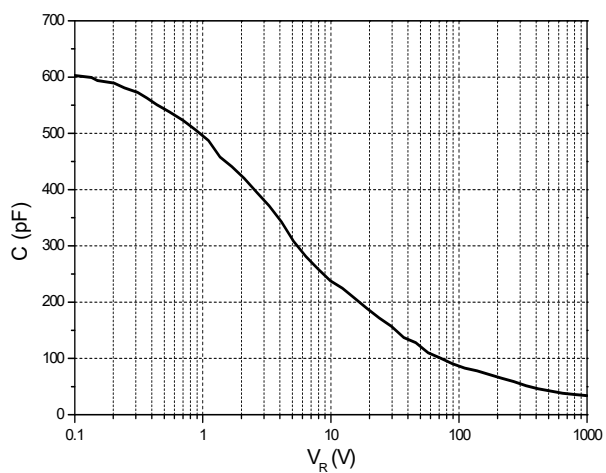


FIG.4: Transient thermal impedance

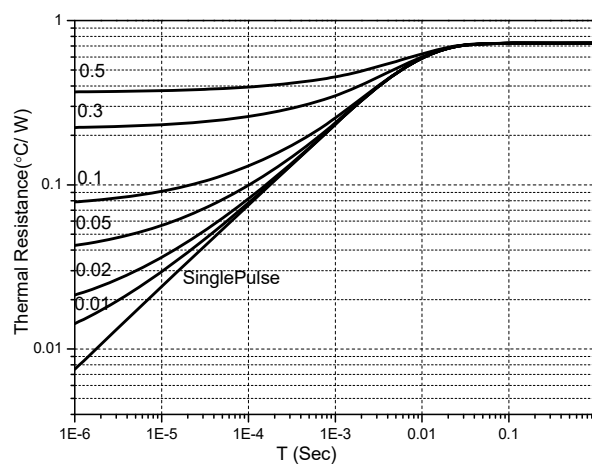


FIG.5: Capacitance charge vs. reverse voltage

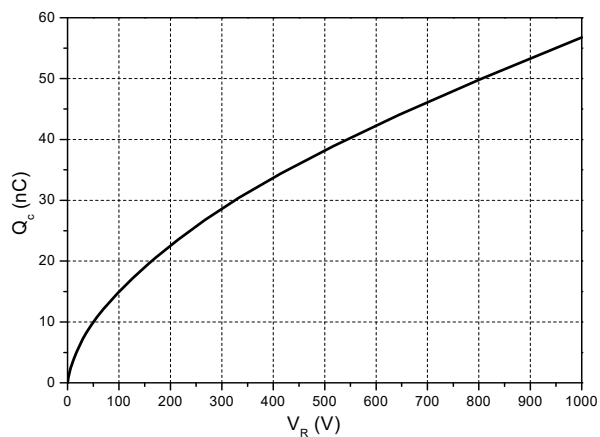


FIG.6: Capacitance stored energy

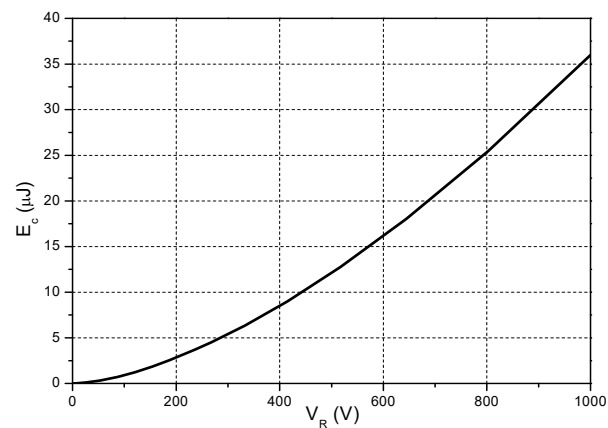


FIG.7: Power derating

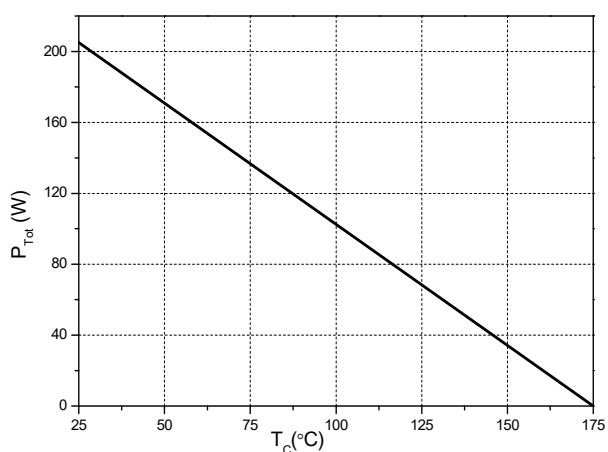
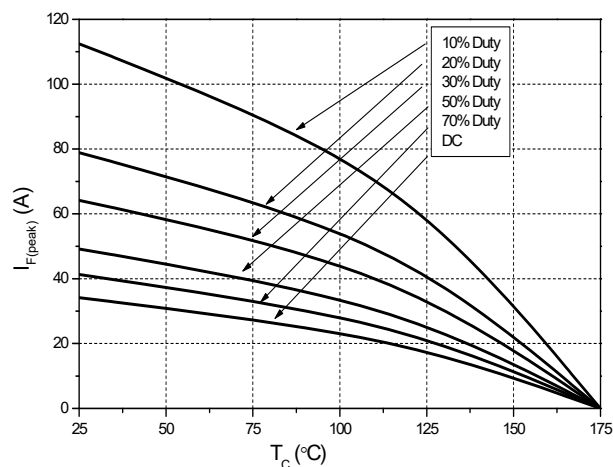


FIG.8: Current derating



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